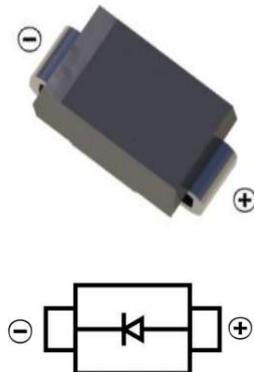


SMC General Purpose Rectifier Diode 通用整流二极管**■Features 特点**

Glass passivated junction 玻璃钝化结
 Low reverse leakage current 低反向漏电流
 Low forward voltage drop 低正向压降
 High current capability 高电流能力
 Surface mount device 表面贴装器件
 Case 封装: SMC(DO-214AB)

**■Maximum Rating 最大额定值**

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	S10 AC	S10 BC	S10 DC	S10 GC	S10 JC	S10 KC	S10 MC	Unit 单位
Marking 印字		S10A	S10B	S10D	S10G	S10J	S10K	S10M	
Peak Reverse Voltage 反向峰值电压	V _{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage RMS 反向电压	V _{R(RMS)}	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I _F				10				A
Peak Surge Current 峰值浪涌电流	I _{FSM}				175				A
Thermal Resistance J-A 结到环境热阻	R _{θJA}				13				°C/W
Junction and Storage Temperature 结温和储藏温度	T _J , T _{stg}				150°C, -65 to +150°C				

■Electrical Characteristics 电特性

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压	V _F			1.1	V	I _F =10A
Reverse Current 反向电流	I _R	(T _A =25°C) (T _A =125°C)		5 250	uA	V _R =V _{RRM}
Diode Capacitance 二极管电容	C _D		70		pF	V _R =4V, f=1MHz

■Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD

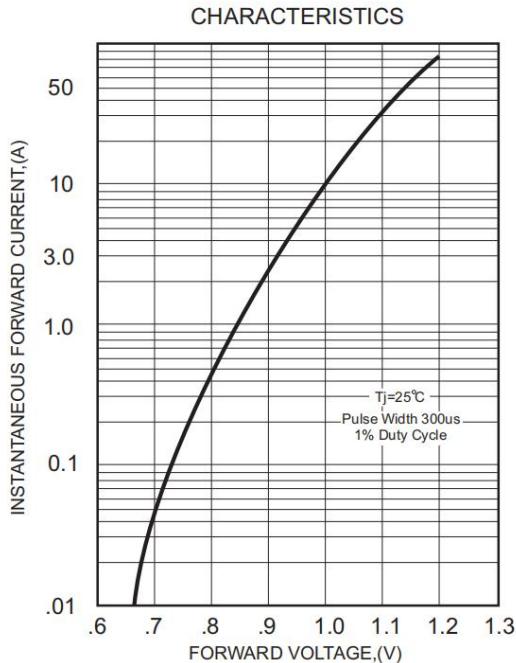


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

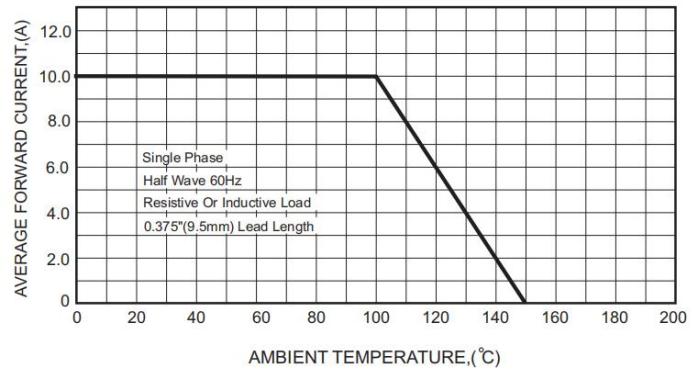


FIG.3 - TYPICAL REVERSE

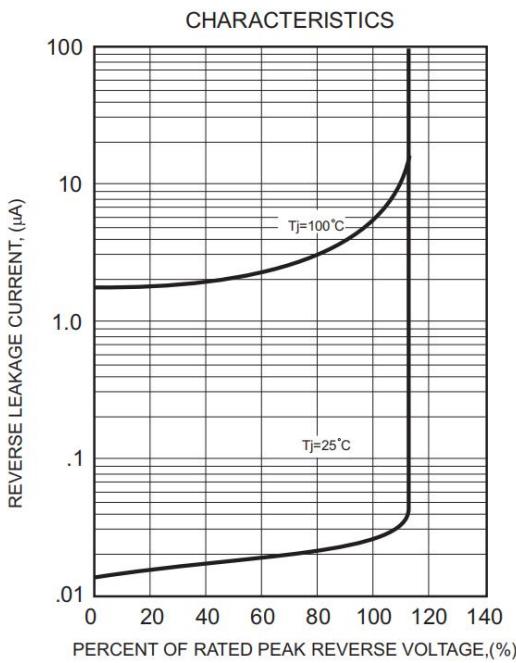


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

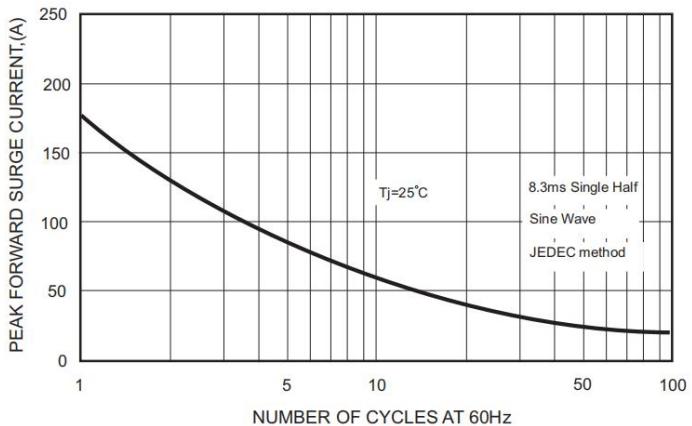
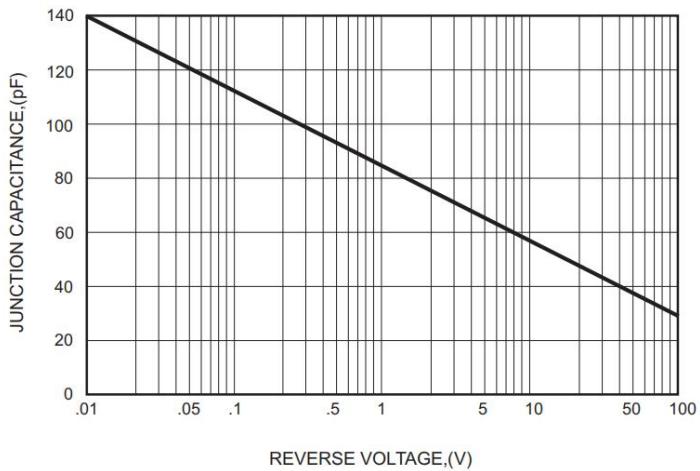
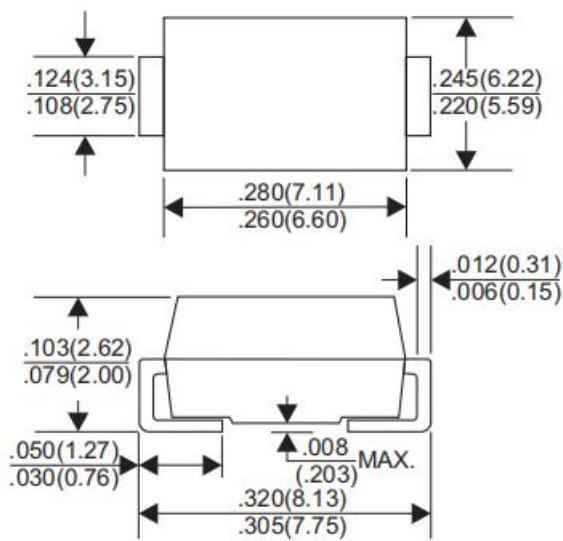


FIG.5-TYPICAL JUNCTION CAPACITANCE



■Dimension 外形封装尺寸

DO-214AB(SMC)



Dimensions in inches and (millimeters)